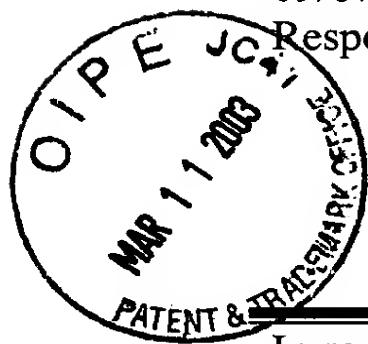


09/678,414

Response to Office Action Mailed December 4, 2002

# 16/D  
PATENT

3/19/03  
Smith



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

David W. Carlson

Appln. No.: 09/678,414

Filed: October 2, 2000

For: METHOD FOR PLANARIZING A THIN FILM

Group Art Unit: 2823

Examiner: B. Kebede

RESPONSE TO OFFICE ACTION MAILED  
DECEMBER 4, 2002

**CERTIFICATE OF MAILING**

I hereby certify that this correspondence is being deposited with the United States Postal Service, postage prepaid, in an envelope,

addressed to Box \_\_\_\_\_, Commissioner for Patents,  
Washington D.C. 20231-9999 on March 4, 2003

✓ Dated: 03-04-03

By: [Signature]

Commissioner for Patents  
Washington, D.C. 20231

Dear Sir:

In response to the Official Action mailed December 4, 2002, please amend the above-identified application as follows:

In the Claims

The claims have been amended to read as follows:

D 1. (Twice Amended) A method for forming a planarized layer of material on a processed wafer, the wafer having a top surface, the top surface having spaced-apart wafer upper levels and a wafer lower level that lies between the wafer upper levels, the wafer upper levels lying above the wafer lower level, the method comprising the steps of:

forming a layer of first material on the top surface of the wafer, the layer of first material having a top surface, the top surface of the layer of first material having a first lower level and a first upper level that lies above the first lower level;

forming a layer of second material on the top surface of the layer of first material; and chemically-mechanically polishing the layer of second material and the underlying layer of first material with a slurry until the layer of second material is substantially all removed from the layer of first material to form the planarized layer of material, the planarized layer of material lying over the wafer upper levels and the wafer lower level.

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